

Silicon PNP Power Transistors

2SB1094

DESCRIPTION

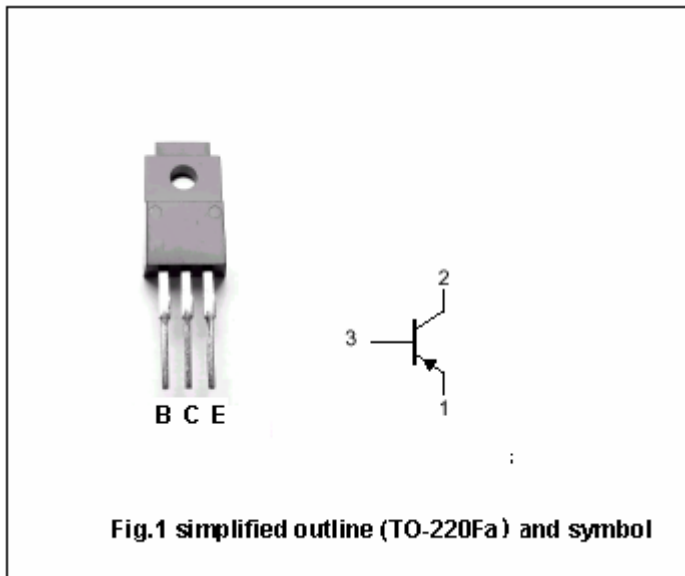
- With TO-220Fa package
- Complement to type 2SD1585

APPLICATIONS

- Ideal for power supplies or variety or in audio and other equipment

PINNING

PIN	DESCRIPTION
1	Emitter
2	Collector
3	Base



Absolute maximum ratings(Ta=25°C)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	Open emitter	-60	V
V _{CEO}	Collector -emitter voltage	Open base	-60	V
V _{EBO}	Emitter-base voltage	Open collector	-7	V
I _C	Collector current		-3	A
I _{CM}	Collector current-peak		-5	A
I _B	Base current		-0.6	A
P _C	Collector power dissipation	T _a =25°C	2.0	W
		T _C =25°C	15	
T _j	Junction temperature		150	°C
T _{stg}	Storage temperature		-55~150	°C

Silicon PNP Power Transistors

2SB1094

CHARACTERISTICS

T_j=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{CEO}	Collector-emitter voltage	I _C =-30mA; I _B =0	-60			V
V _{CEsat}	Collector-emitter saturation voltage	I _C =-2A ; I _B =-0.2A			-1.5	V
V _{BEsat}	Base-emitter saturation voltage	I _C =-2A ; I _B =-0.2A			-2.0	V
I _{CBO}	Collector cut-off current	V _{CB} =-60V; I _E =0			-10	μA
I _{EBO}	Emitter cut-off current	V _{EB} =-7V; I _C =0			-10	μA
h _{FE-1}	DC current gain	I _C =-50mA ; V _{CE} =-5V	20			
h _{FE-2}	DC current gain	I _C =-0.5A ; V _{CE} =-5V	40		200	
f _T	Transition frequency	I _C =-0.1A; V _{CE} =-5V		20		MHz
C _{OB}	Collector output capacitance	f=1MHz ; V _{CB} =-10V		70		pF

◆ h_{FE-2} Classifications

M	L	K
40-80	60-120	100-200

Silicon PNP Power Transistors

2SB1094

PACKAGE OUTLINE



Fig.2 Outline dimensions (unindicated tolerance: ± 0.15 mm)